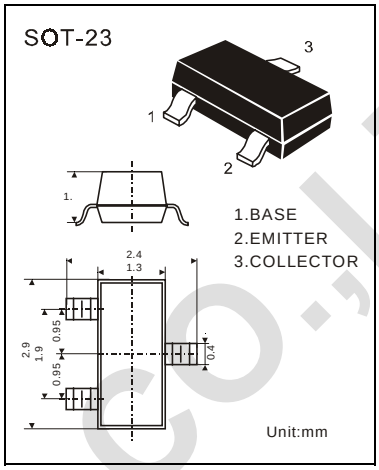
NPN EPITAXIAL SILICON TRANSISTOR

AM/FM IF AMPLIFIER,LOCAL OSCILIATOR OF FM/VHF TUNER

* High Current Gain Bandwidth Product f_T=1100MHz



ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	40	V
Collector-Emitter Voltage	Vceo	30	V
Emitter-Base Voltage	Vebo	4.0	V
Collector Current	Ic	20	mA
Collector Dissipation Ta=25℃*	P_D	100	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	Bvcbo	40			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	Bvceo	30			V	Ic= 1mA Ib=0
Emitter-Base Breakdown Voltage	Bvebo	4.0			V	Ie= 100uA Ic=0
Collector-Base Cutoff Current	Icbo			500	nA	Vcb= 18V Ie=0
Emitter-Base Cutoff Current	Iebo			500	nA	Veb= 4V Ic= 0
DC Current Gain	Hfe	40		200		Vce= 6V Ic= 1mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.40	V	Ic= 10mA Ib= 1mA
Collector-Base Capacitance	Cob		1.3	1.7	PF	Vcb=10V Ie=0 f=1MHZ
Current Gain-Bandwidth Product	f_T		550		MHz	Vce= 6V Ic= 1mA

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25℃.

\# Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

WEJ ELECTRONIC CO.,LTD